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STMicroelectronics STTH16003TV1

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## STTH16003

## High frequency secondary rectifier

### **Features**

- Combines highest recovery and reverse voltage performance
- Ultra-fast, soft and noise-free recovery
- Insulated package: ISOTOP
  - insulated voltage: 2500 V rms
  - capacitance: < 45 pF
- Low inductance and low capacitance allow simplified layout

## **Description**

Dual rectifiers suited for switch mode power supply and high frequency DC to DC converters.

Packaged in ISOTOP, this device is intended for use in low voltage, high frequency inverters, free wheeling operation, welding equipment and telecom power supplies.

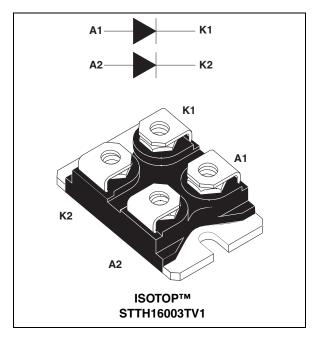


Table 1. Device summary

I <sub>F(AV)</sub>	2 x 60 A
V <sub>RRM</sub>	300 V
T <sub>j</sub>	150 °C
V <sub>F</sub> (typ)	0.95 V
t <sub>rr</sub> (typ)	80 ns

TM: ISOTOP is a registered trademark of STMicroelectronics



Characteristics STTH16003

### 1 Characteristics

Table 2. Absolute ratings (limiting values, per diode, T<sub>amb</sub> = 25 °C unless otherwise stated)

Symbol	Parame	Value	Unit		
$V_{RRM}$	Repetitive peak reverse voltage	300	V		
I <sub>F(RMS)</sub>	RMS forward current			180	Α
I <sub>F(AV)</sub>	Average forward current	$Tc = 85^{\circ}C$ $\delta = 0.5$ Per diode Per device		60 160	Α
I <sub>FSM</sub>	Surge non repetitive forward current	t <sub>p</sub> = 10 ms Sinusoidal	800	Α	
I <sub>RSM</sub>	Non repetitive peak reverse current	t <sub>p</sub> = 100 μs square	5	Α	
T <sub>stg</sub>	Storage temperature range			-55 to + 150	°C
Tj	Maximum operating junction temperature			150	°C

### Table 3. Thermal parameters

Symbol	Parameter		Maximum	Unit
D	Junction to case	Per diode	0.7	
R <sub>th(j-c)</sub>	ounction to case	Total	0.4	°C/W
R <sub>th(c)</sub>	Coupling		0.1	

When the diodes 1 and 2 are used simultaneously:

 $\Delta T_{j \text{ (diode1)}} = P_{\text{(diode1)}} x R_{\text{th(j-c) (per diode)}} + P_{\text{(diode2)}} x R_{\text{th(c)}}$ 

 Table 4.
 Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25 °C	V <sub>R</sub> = 300 V			200	μΑ
'R`´	neverse leakage culterit	T <sub>j</sub> = 125 °C	V <sub>R</sub> = 300 V		0.2	2	mA
V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 80 A			1.2	V	
	T <sub>j</sub> = 125 °C	25 °C		0.8	0.95	V	

- 1. Pulse test:  $t_p$  = 5 ms,  $\delta$  < 2 %
- 2. Pulse test:  $t_p = 380 \mu s$ ,  $\delta < 2 \%$ 
  - 1. to evaluate the maximum conduction losses use the following equation: P = 0.75 x  $I_{F(AV)}$  + 0.0025  $I_{F}^{2}_{(RMS)}$





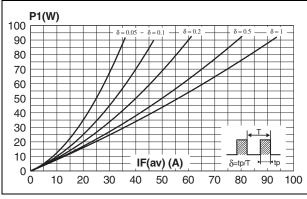
STTH16003 Characteristics

Table 5. Recovery characteristics

Symbol	Parameter	Test conditions			Тур	Max.	Unit
+	Reverse recovery time	T <sub>i</sub> = 25 °C	$I_F = 0.5 \text{ A}, I_{rr} = 0.25 \text{ A}$ $I_R = 1 \text{ A}$			60	ns
t <sub>rr</sub>	Theverse recovery time	1j = 25 0	$I_F = 1$ A, $dI_F/dt = 50$ A/ $\mu$ s, $V_R = 30$ V			80	ns
t <sub>fr</sub>	Forward recovery time	$T_j = 25  ^{\circ}\text{C}$ $I_F = 80  \text{A}$ $dI_F/dt = 200  \text{A/}\mu\text{s}$ $V_{FR} = 1.1  \text{x}  V_{Fmax}$				1000	ns
V <sub>FP</sub>	Forward recovery voltage					5	V
I <sub>RM</sub>	Reverse recovery current	T 125 °C	$I_F = 60 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s},$			16	Α
S <sub>factor</sub>		$T_j = 125  ^{\circ}\text{C}$ $I_F = 60  \text{A},  dI_F/dt = 200  \text{A}/\mu\text{s},$ $V_{cc} = 200  \text{V}$		0.3		-	

Figure 1. Conduction losses versus average current (per diode)

Figure 2. Forward voltage drop versus forward current (maximum values, per diode)



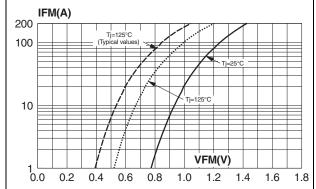
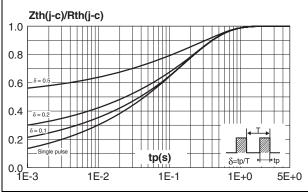
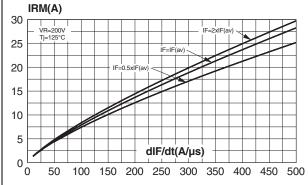


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl<sub>F</sub>/dt (90% confidence, per diode)







Characteristics STTH16003

Figure 5. Reverse recovery time versus dl<sub>F</sub>/dt (90% confidence, per diode)

trr(ns) 240 VR=200V Tj=125°C 220 200 180 160 140 120 100 80 60 40 20 dIF/dt(A/µs) 0 0 100 150 200 250 300 350 400 450 500

Figure 6. Softness factor (tb/ta) versus dI<sub>F</sub>/dt (typical values, per diode)

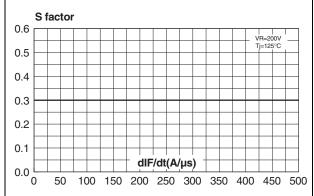


Figure 7. Relative variation of dynamic parameters versus junction temperature (reference: T<sub>i</sub> = 125°C)

2.4 2.2 2.0 S facto 1.8 1.6 1.4 1.2 1.0 0.8 IRM 0.6 0.4 0.2 Tj(°C) 0.0 5 100

Figure 8. Transient peak forward voltage versus dl<sub>F</sub>/dt (90% confidence, per diode)

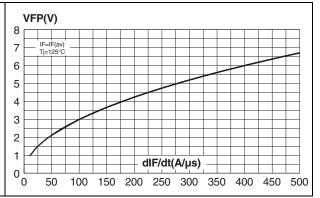
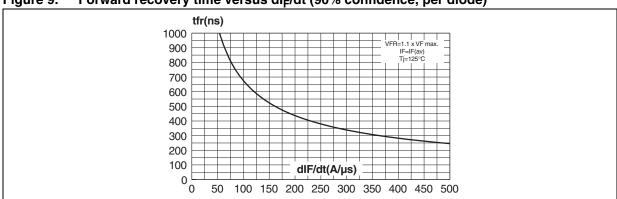


Figure 9. Forward recovery time versus dl<sub>F</sub>/dt (90% confidence, per diode)





STTH16003 Package information

## 2 Package information

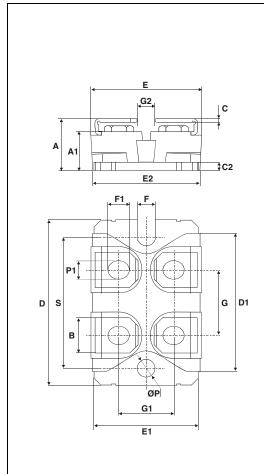
Cooling method: by conduction (C)

■ Recommended torque value: 0.9 to 1.2 N·m

Epoxy meets UL 94,V0

In order to meet environmental requirements, ST offers these devices in ECOPACK<sup>®</sup> packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at <a href="https://www.st.com">www.st.com</a>.

Table 6. ISOTOP dimensions



	Dimensions				
Ref.	Millimeters Min. Max.		Inc	hes	
			Min.	Max.	
Α	11.80	12.20	0.465	0.480	
A1	8.90	9.10	0.350	0.358	
В	7.8	8.20	0.307	0.323	
С	0.75	0.85	0.030	0.033	
C2	1.95	2.05	0.077	0.081	
D	37.80	38.20	1.488	1.504	
D1	31.50	31.70	1.240	1.248	
Е	25.15	25.50	0.990	1.004	
E1	23.85	24.15	0.939	0.951	
E2	24.80 typ.		0.97	6 typ.	
G	14.90	15.10	0.587	0.594	
G1	12.60	12.80	0.496	0.504	
G2	3.50	4.30	0.138	0.169	
F	4.10	4.30	0.161	0.169	
F1	4.60	5.00	0.181	0.197	
Р	4.00	4.30	0.157	0.69	
P1	4.00	4.40	0.157	0.173	
S	30.10	30.30	1.185	1.193	





**Ordering information** 

STTH16003

# 3 Ordering information

 Table 7.
 Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH16003TV1	STTH16003TV1	ISOTOP	27 g (without screws)	10 (with screws)	Tube

# 4 Revision history

Table 8. Document revision history

Date	Revision	Description of changes
Oct-1999	4D	Last issue.
25-Jun-2008	5	Reformatted to current standards. Corrected marking in Table 7

### Distributor of STMicroelectronics: Excellent Integrated System Limited

Datasheet of STTH16003TV1 - DIODE MODULE 300V 60A ISOTOP

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#### STTH16003

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